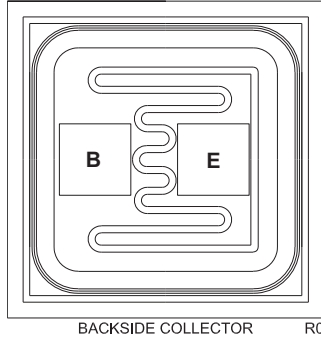


CP336V-2N5551

NPN - High Voltage Transistor Die

The CP336V-2N5551 is a silicon NPN transistor designed for high voltage, general purpose applications.



MECHANICAL SPECIFICATIONS:

Die Size	17.3 x 17.3 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Size	3.9 x 3.9 MILS
Emitter Bonding Pad Size	3.9 x 3.9 MILS
Top Side Metalization	Al-Si – 17,000Å
Back Side Metalization	Au – 9,000Å
Scribe Alley Width	1.8 MILS
Wafer Diameter	5 INCHES
Gross Die Per Wafer	57,735

MAXIMUM RATINGS: (T_A=25°C)

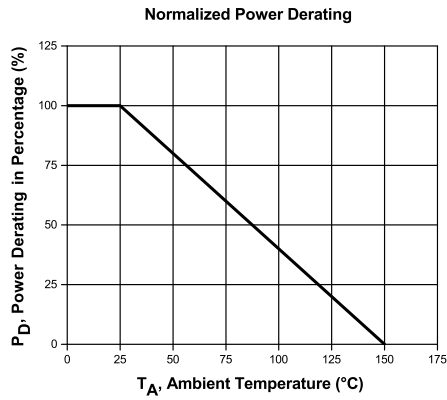
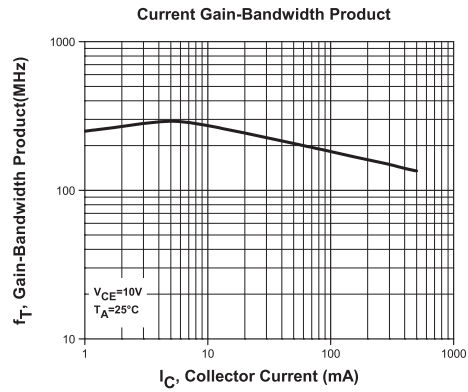
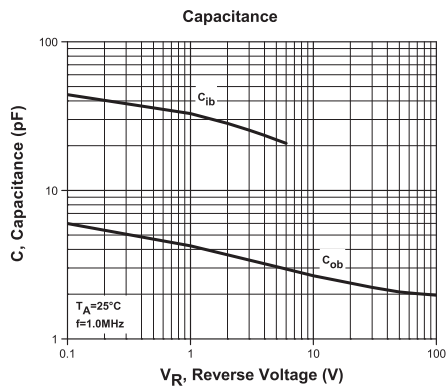
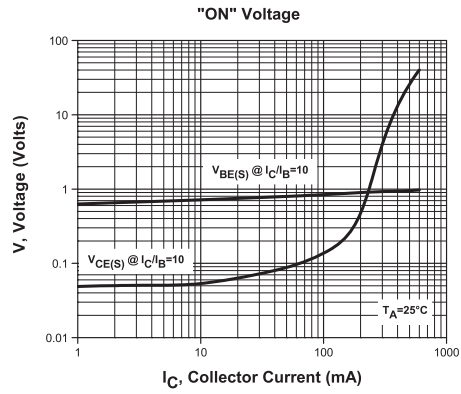
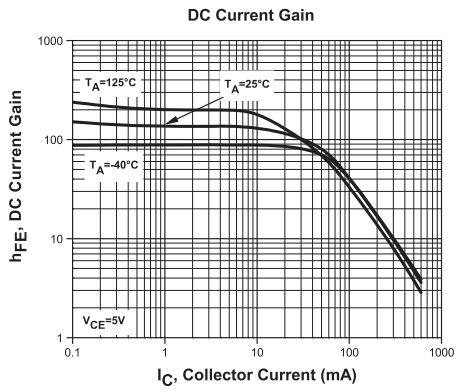
	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Continuous Collector Current	I _C	600	mA
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =120V		50	nA
I _{EBO}	V _{EB} =4.0V		50	nA
BV _{CB0}	I _C =100μA	180		V
BV _{CEO}	I _C =1.0mA	160		V
BV _{EBO}	I _E =10μA	6.0		V
V _{CE(SAT)}	I _C =10mA, I _B =1.0mA		0.15	V
V _{CE(SAT)}	I _C =50mA, I _B =5.0mA		0.20	V
V _{BE(SAT)}	I _C =50mA, I _B =5.0mA		1.0	V
h _{FE}	V _{CE} =5.0V, I _C =1.0mA	80		
h _{FE}	V _{CE} =5.0V, I _C =10mA	80	250	
h _{FE}	V _{CE} =5.0V, I _C =50mA	30		
f _T	V _{CE} =10V, I _C =10mA, f=100MHz	100	300	MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		6.0	pF

CP336V-2N5551

Typical Electrical Characteristics



OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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